

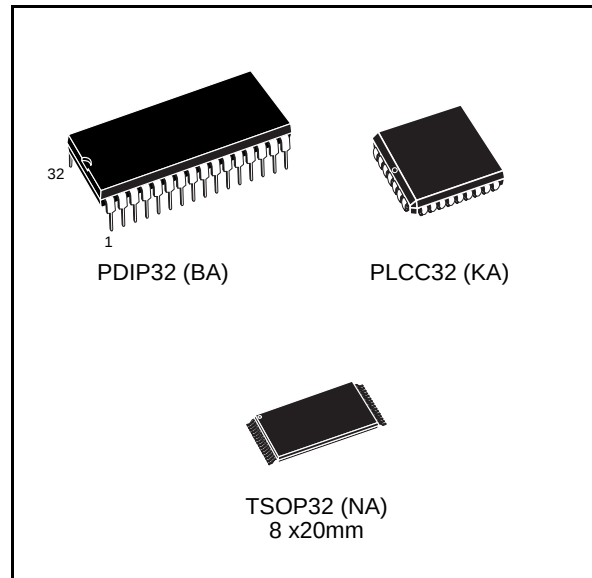
1Mbit (128Kb x8) Parallel EEPROM with Software Data Protection

DATA BRIEFING

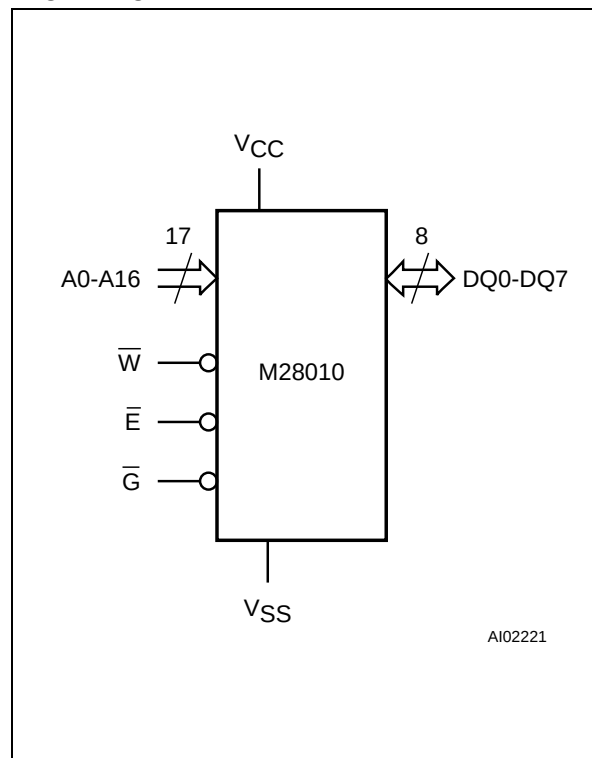
- FAST ACCESS TIME: 100ns
- 2.7V to 3.6V SINGLE SUPPLY VOLTAGE
- LOW POWER CONSUMPTION
- FAST WRITE CYCLE:
 - 128 Bytes Page Write Operation
 - Byte or Page Write Cycle
- ENHANCED END of WRITE DETECTION:
 - Data Polling
 - Toggle Bit
- PAGE LOAD TIMER STATUS BIT for START of WRITE DETECTION
- STATUS REGISTER
- HIGH RELIABILITY DOUBLE POLYSILICON, CMOS TECHNOLOGY:
 - Endurance >100,000 Erase/Write Cycles
 - Data Retention >10 Years
- JEDEC APPROVED BYTEWISE PIN OUT and STANDARD COMMANDS
- SOFTWARE DATA PROTECTION
- HARDWARE WRITE PROTECTION
- SOFTWARE CHIP ERASE

DESCRIPTION

The M28010 is a 128 Kbit x 8 low power Parallel EEPROM fabricated with SGS-THOMSON proprietary double polysilicon CMOS technology. The devices offer fast access time with low power dissipation and requires a 2.7V to 3.6V power supply. The circuit has been designed to offer a flexible microcontroller interface featuring both hardware and software handshaking with Data Polling and Toggle Bit and access to a status register. The devices support a 128 byte page write operation. A Software Data Protection (SDP) and Software Chip Erase are also possible using the standard JEDEC algorithm.

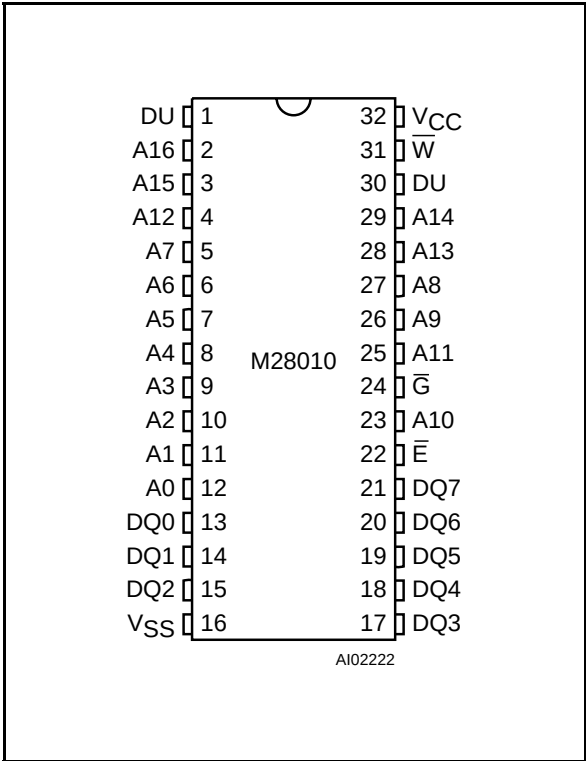


Logic Diagram



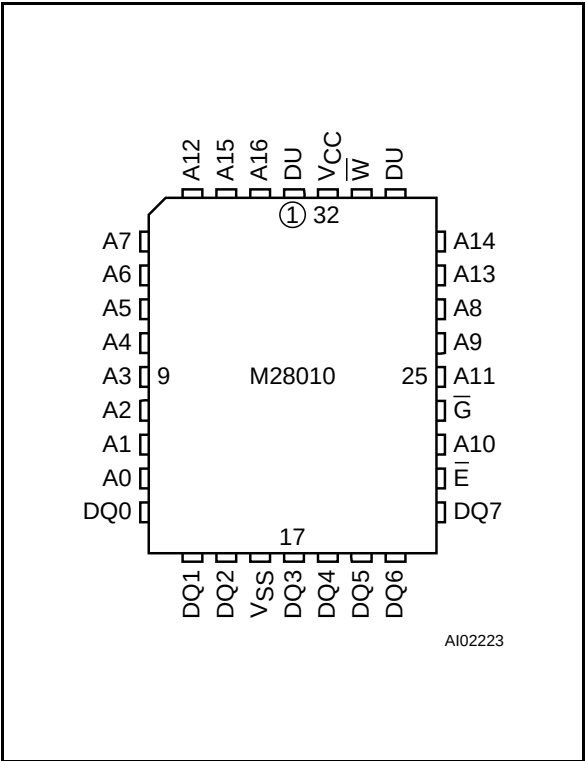
M28010

DIP Pin Connections



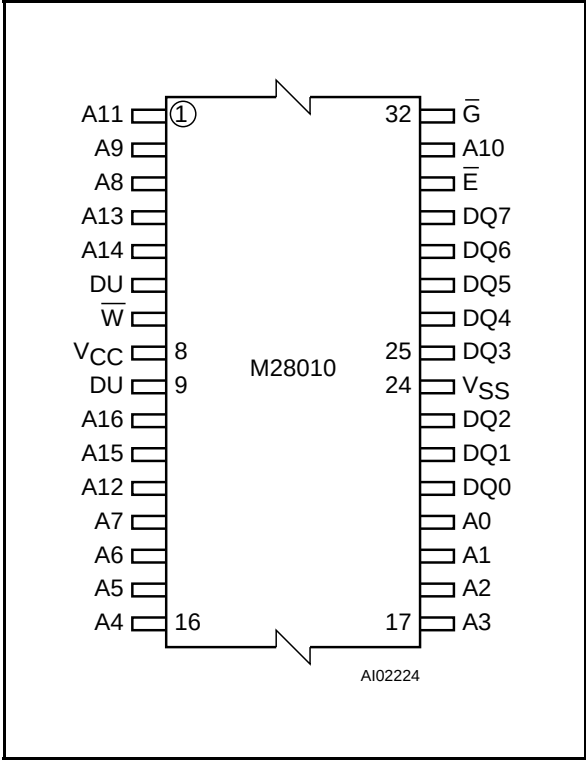
Warning: DU = Don't Use.

LCC Pin Connections



Warning: DU = Don't Use.

TSOP Pin Connections

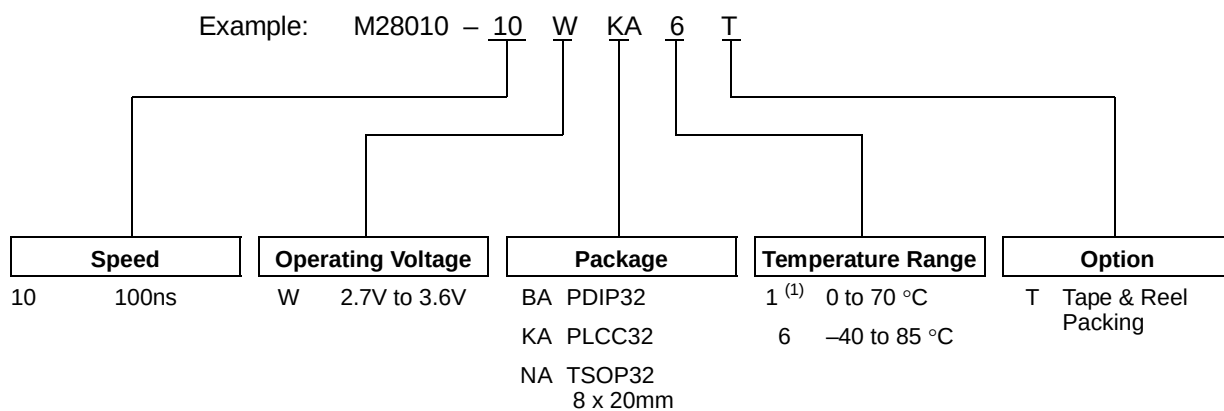


Warning: DU = Don't Use.

Signal Names

A0-A16	Address Input
DQ0-DQ7	Data Input / Output
W-bar	Write Enable
E-bar	Chip Enable
G-bar	Output Enable
V _{CC}	Supply Voltage
V _{SS}	Ground

ORDERING INFORMATION SCHEME



Note: 1. Temperature Range on request only.

Devices are shipped from the factory with the memory content set at all "1's" (FFh).

For a list of available options (Speed, Package, etc...) or for further information on any aspect of this device, please contact the SGS-THOMSON Sales Office nearest to you.